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(NASA-CR-161827) CHARGE INJECTION DEVICE  
EVALUATION HARDWARE Final Report (Bendix  
Corp.) 17 p HC A02/MF A01 CSCL 09C

N81-28355

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**FINAL REPORT  
CHARGE INJECTION  
DEVICE EVALUATION  
HARDWARE**

**CONTRACT NO.  
NAS 8-33740**

**Prepared for:**

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**April 30, 1981**



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## 1.0 INTRODUCTION

Star trackers typically employ photomultiplier/image dissector type devices as detection sensors. These devices are large and bulky, adding weight and volume to end-item physical characteristics. They require thousands of volts bias for proper operation, thereby necessitating use of proper protection at the detector tube and power supply level to guard against potential, catastrophic arcing problems in a space environment. They require magnetic shielding and a shutter mechanism for photocathode protection against possible sunlight damage.

Better versatility and flexibility would be achieved if solid state detectors could be utilized as alternate devices. They are small and light, requiring only a few volts reverse bias at almost zero power. They do not need magnetic shielding of any kind and they have sufficient sensitivity characteristics to make them candidates for star sensor applications and, most important, they are not susceptible to damage from high light levels. They can survive when the sun is focussed directly onto them and can tolerate being heated by such means to several hundred degrees centigrade without permanent damage. Charge Injection Devices (CID's) appear to promise this capability.

## 2.0 OBJECTIVE

The objective of this effort was to develop a versatile test tool to evaluate candidate CID detectors. This resulted in the design and fabrication of a microprocessor based system which provides maximum testing flexibility via

software reconfiguration. This system has the capability to evaluate a charge injection device (CID) and to characterize its performance. The construction and operation of the CID offers several significant advantages over the various CCD configurations currently available. Among these advantages are:

- o Less sophisticated manufacturing processes required than for CCD's. Results in potentially lower fabrication costs and higher yields.
- o Virtually no obscuration (i.e., dead zones) between pixels (interline transfer CCDS have 50%) results in high optical gain and no distortion of the interpolation function.
- o No image smearing during readout (as in frame transfer CCD's) allows continuous exposure without shuttering the optical input.
- o High resistance to blooming due to optical overload permits detection of dim targets near bright sources.
- o High transfer efficiencies (i.e.,  $>0.999$ ) not required due to low (by several orders of magnitude compared to CCD's) number of transfer operations required to read a pixel.
- o Insensitivity to transfer efficiency variations provides improved tolerance to degradation mechanisms (e.g., radiation).

### 3.0 CHARGE INJECTION DEVICE (CID) CONFIGURATION

The CID is organized as an array of 128 by 128 picture elements (pixels). A 30 $\mu$ m pixel spacing provides an active photosensitive area of about 0.145 sq. cm. A simplified CID layout is shown in Figure 1.

The array is divided into 1024 blocks, each consisting of 4x4 pixels. Any given block is selected via on-chip horizontal (column) and vertical (row) shift registers. Enable lines (E1 through E4) transfer signal charge for a single column from pixel collection sites to corresponding output sites. Signals from all four rows are available simultaneously (parallel outputs) for processing.

Subsequent rows are read-out by first returning the signal charge for the current row back to the collection site and then transferring the signal for the next row. This non-destructive readout method is continued until all of the desired blocks have been interrogated. At this point, all of the signal charge in the entire array is injected into the substrate to reset the collection sites for the next integration period (frame).

The above CID readout method is but one of several possible alternatives made available by the configuration of the device to be evaluated. This, in part, is due to the relatively large number of control lines brought to the external pinout.

Due to its unique timing and voltage level requirements, evaluation of the CID in a previously constructed CCD breadboard was not possible without extensive modification.



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Furthermore, the exploration of various readout methods and processing techniques may require additional complex circuitry. Thus a separate CID breadboard, under the control of a microprocessor, will provide a more expedient approach to device evaluation.

#### 4.0 CID BREADBOARD

A block diagram of the CID breadboard is shown in Figure 2. The micro-processor ( $\mu$ P) based test configuration provides maximum flexibility to explore various CID readout and signal processing techniques.

The CID is housed in a small thermal-vacuum chamber to provide a controlled temperature environment. An optical window on the chamber passes light from an external test source/imaging assembly to the photo-sensitive array. The control signals required to operate the CID are generated by the microprocessor under software control. Level shifters are required to convert the TTL logic levels to appropriate MOS values.

The signal processing electronics consist of four high gain, low-noise preamplifiers, companion sample-and-hold (S/H) circuits and a multiplexed analog-to-digital (A/D) converter. This configuration is necessary to convert the parallel CID output to a serial  $\mu$ P input.

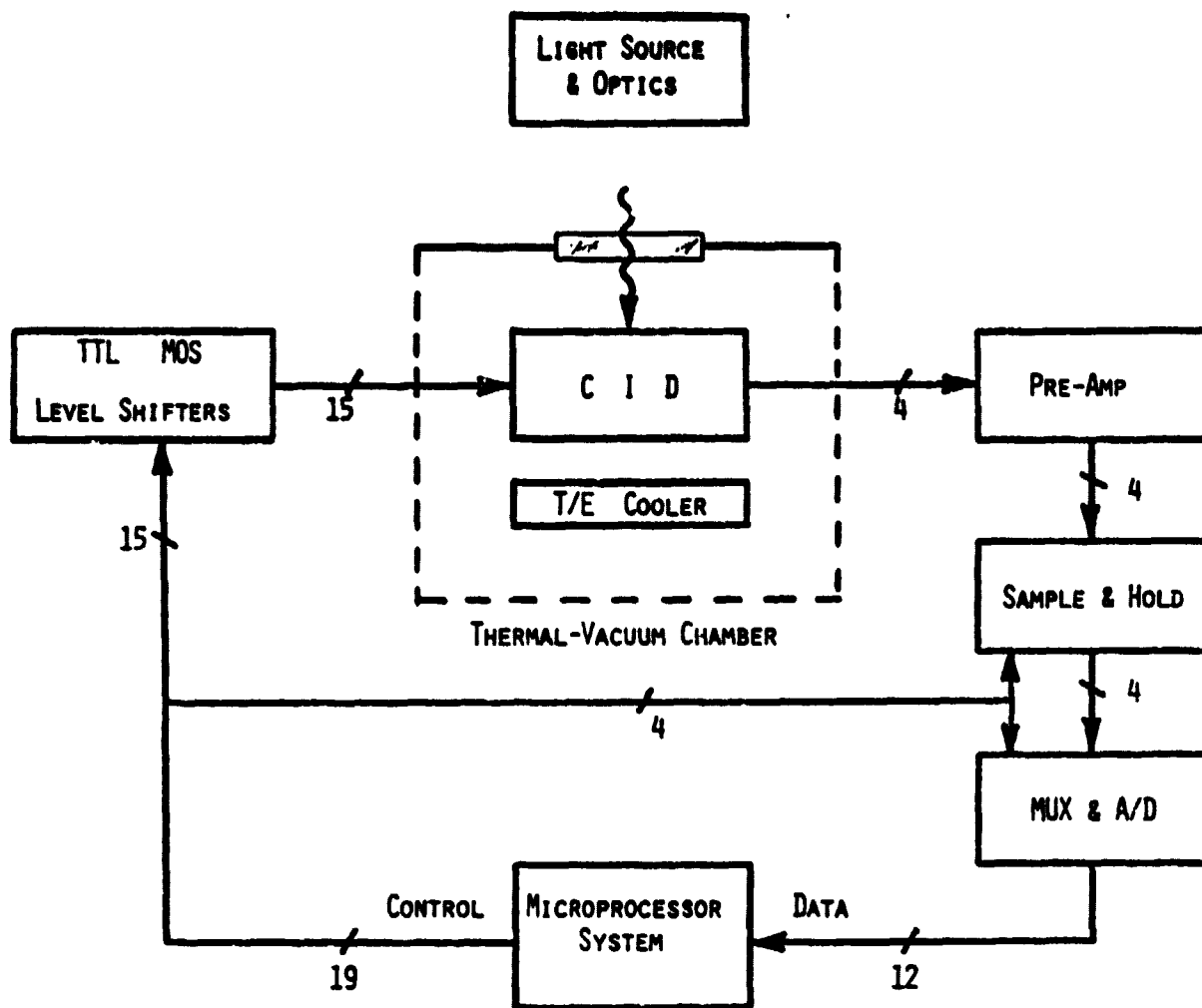
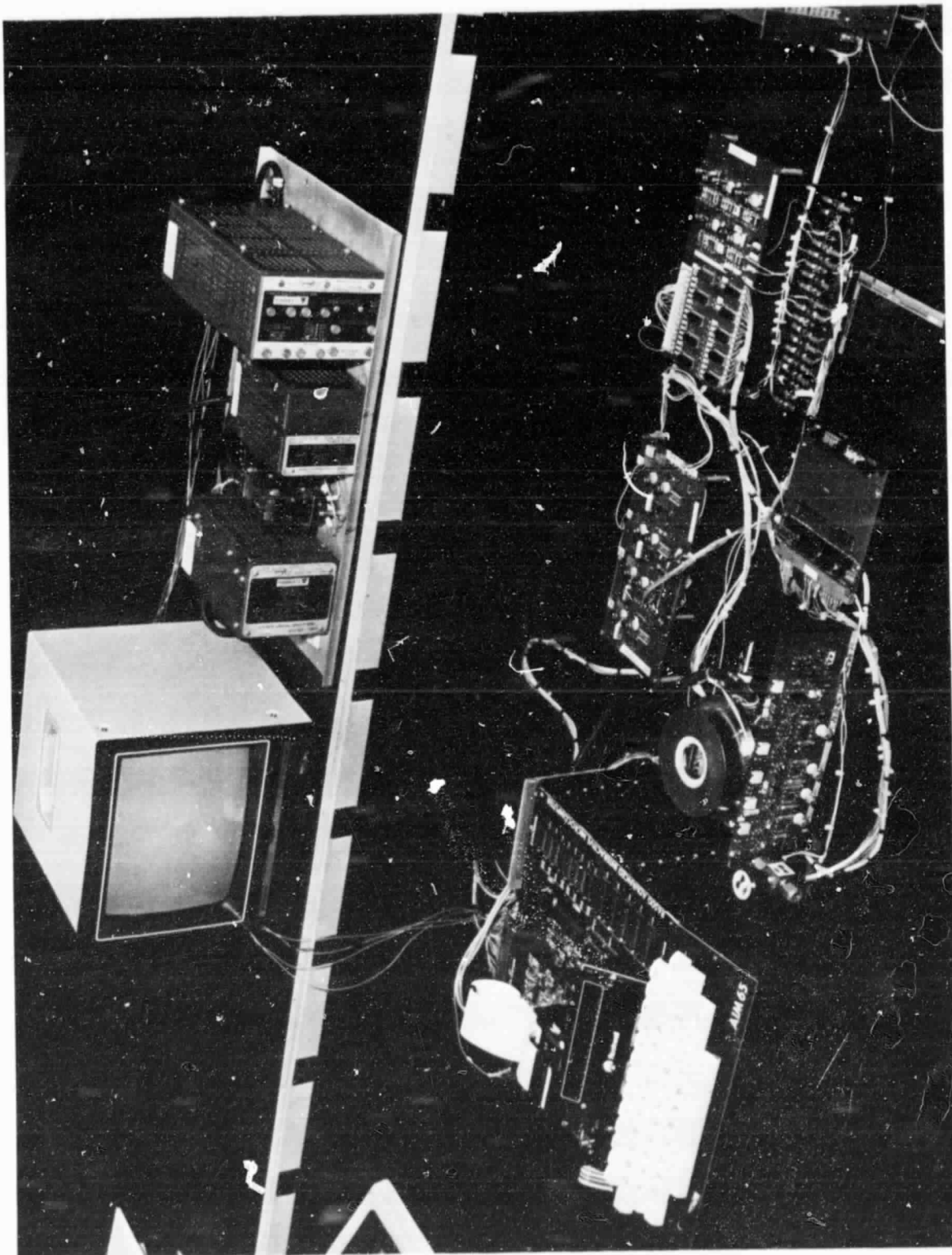


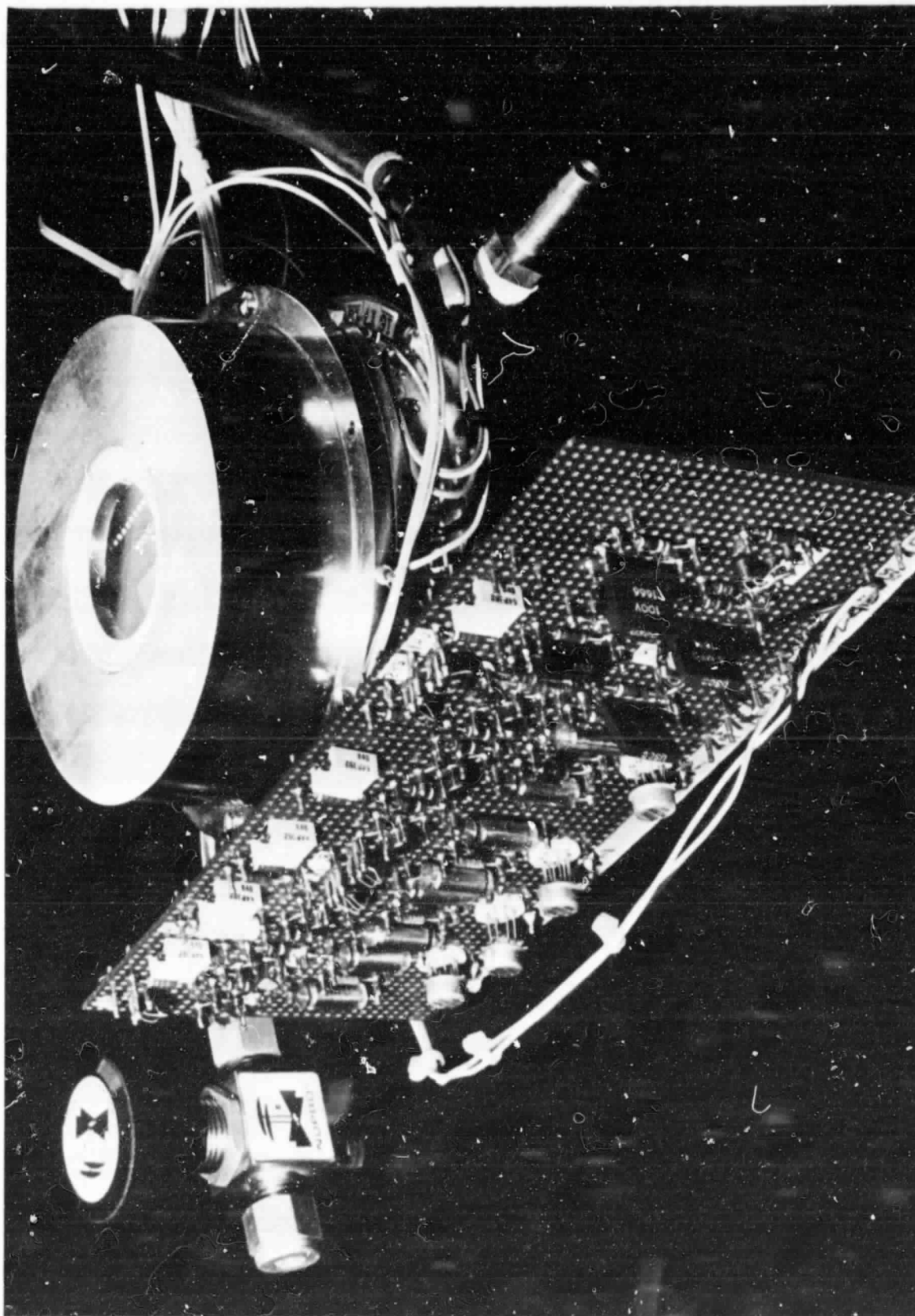
FIGURE 2  
C I D EVALUATION BREADBOARD BLOCK DIAGRAM





CID EVALUATION BREADBOARD

ORIGINAL PAGE IS  
OF POOR QUALITY



CID T/V CHAMBER & PRE-AMP

### MICROPROCESSOR

The CID evaluation breadboard incorporates a microprocessor to perform three distinct tasks: 1. CID/Electronics control, 2. Data Collection, 3. Data Processing. Control and collection operations are shared during a given test in real time whereas processing is performed "off-line" after sufficient data is collected.

A block diagram of the microprocessor and support equipment is shown in Figure 3. A single board computer (Rockwell AIM65) utilizes a 6502 microprocessor operating at one megahertz. Build in serial I/O is used for communication with a CRT terminal and printer during software development.

Since the worst case memory requirement for data storage is 16K bytes, this exceeds the 4K on-board capability. A memory extension was added to provide a total of 32K of data and programming space. The memory extension board (DRAM) also provides the additional programmable I/O Ports (6522's) required for the control signals.

A graphics board generates a visual representation of the CID perceived image and provides a means of interactive communication between operator and machine (keyboard input is part of the main CPU board).

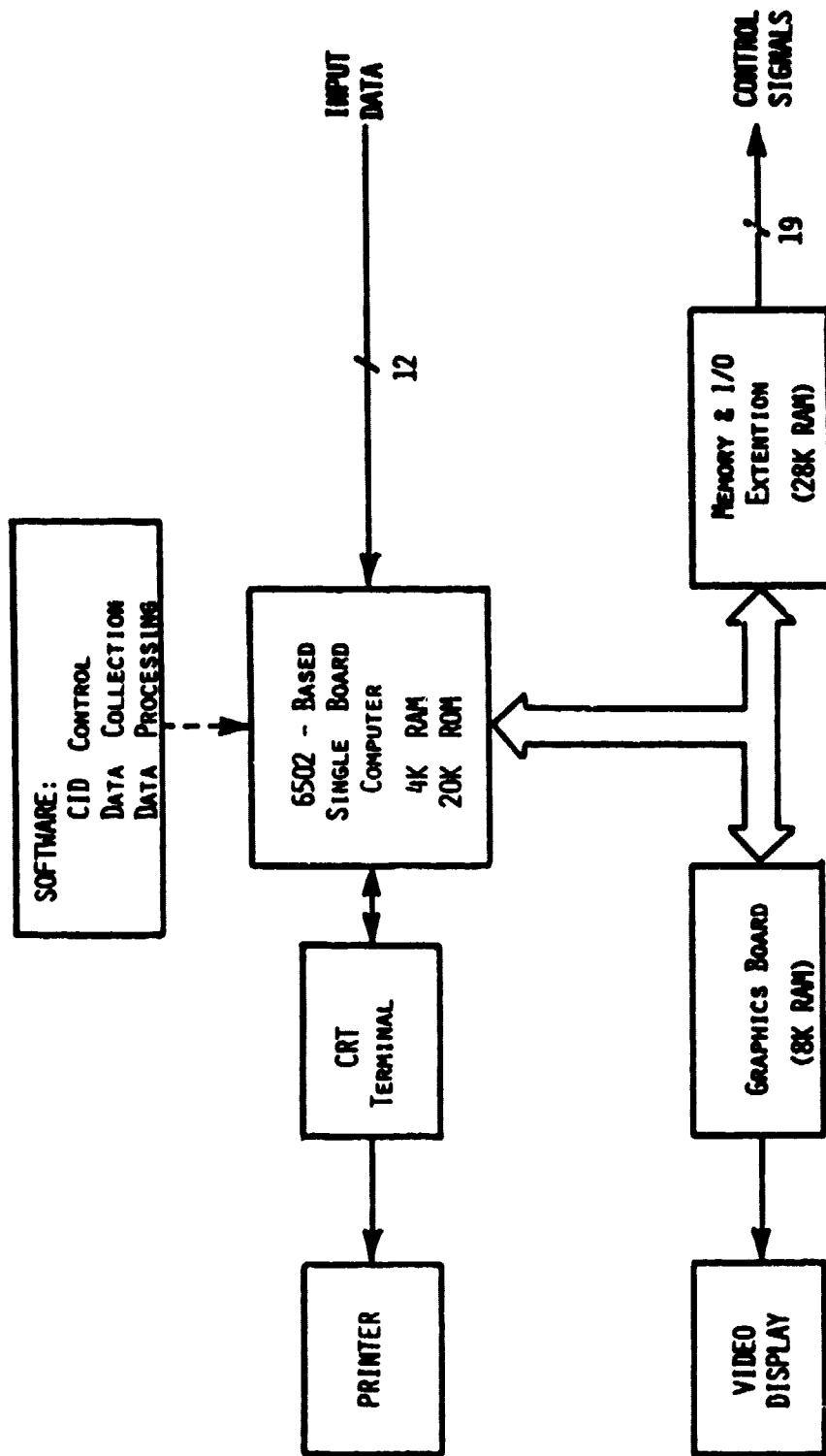


FIGURE 3  
MICROPROCESSOR SYSTEM DIAGRAM

## SOFTWARE

The CID evaluation software consists of an "executive" and supporting subroutines. A menu approach presents a list of options for the operator to consider (see Figure 4). This allows for convenient control over data collection and data processing operations.

The bulk of the software is written in a high level language (i.e., BASIC) to minimize initial development time and to simplify the implementation of program modifications downstream. Time-critical operations, of course, are written in machine code. This includes all CID control and data gathering functions.

## TIME CONSIDERATIONS

Although a microprocessor based system offers maximum flexibility with minimum hardware, this advantage is often gained at the expense of operating speed. The design of the CID control software must therefore consider methods to minimize pixel readout time.

During the readout cycle the microprocessor operates the control lines to the CID, sample-and-hold, multiplexer and analog-to-digital converter. In addition, it must read the data from the A/D and perform limited processing.

Figure 5 illustrates one approach of reading the four rows of one column of a selected block. First, the signals from all four rows are gated to the output lines (previously reset) by enabling the appropriate column. Next, the signals

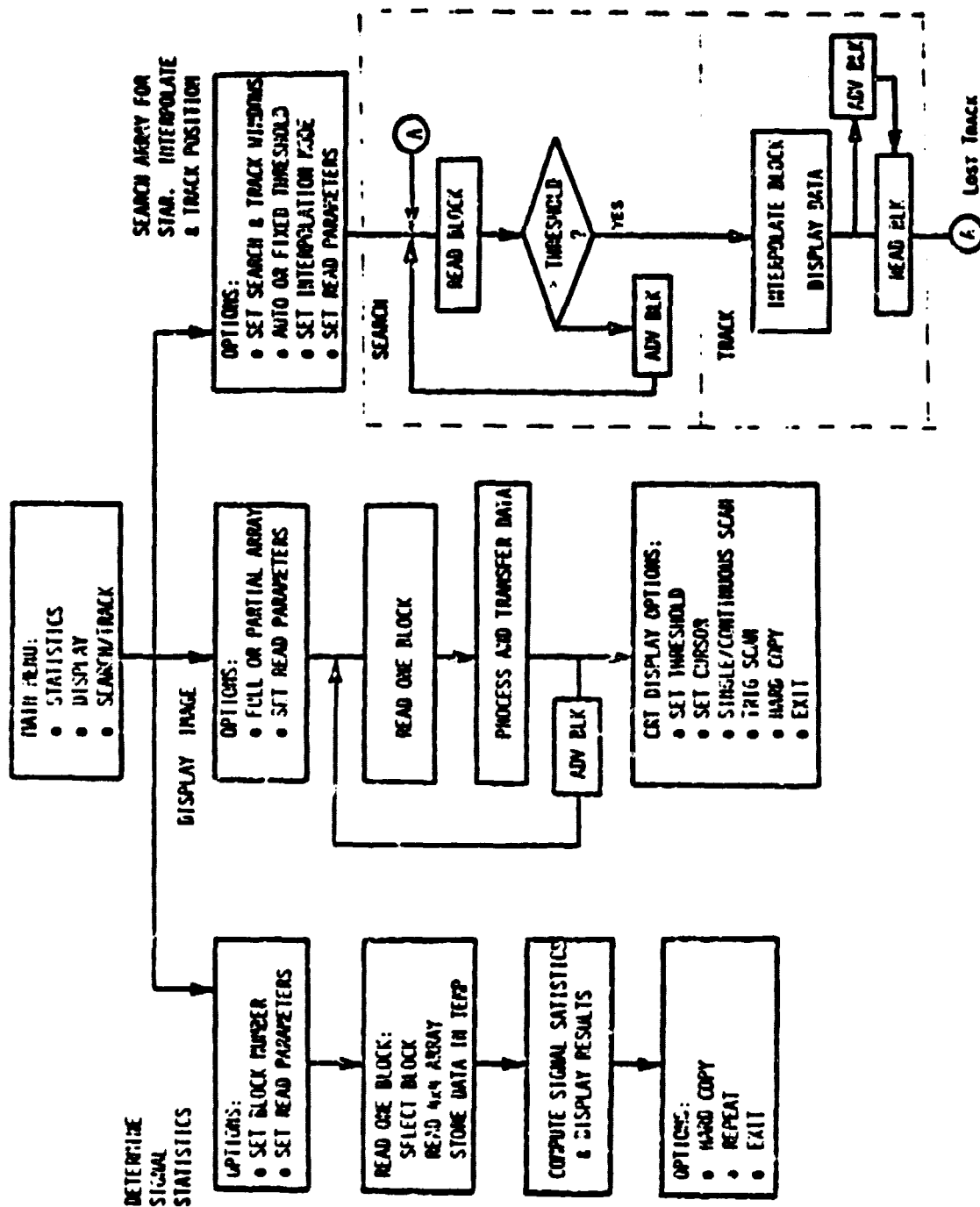


FIGURE 4

C13 EVALUATION SOFTWARE  
(PRELIMINARY)

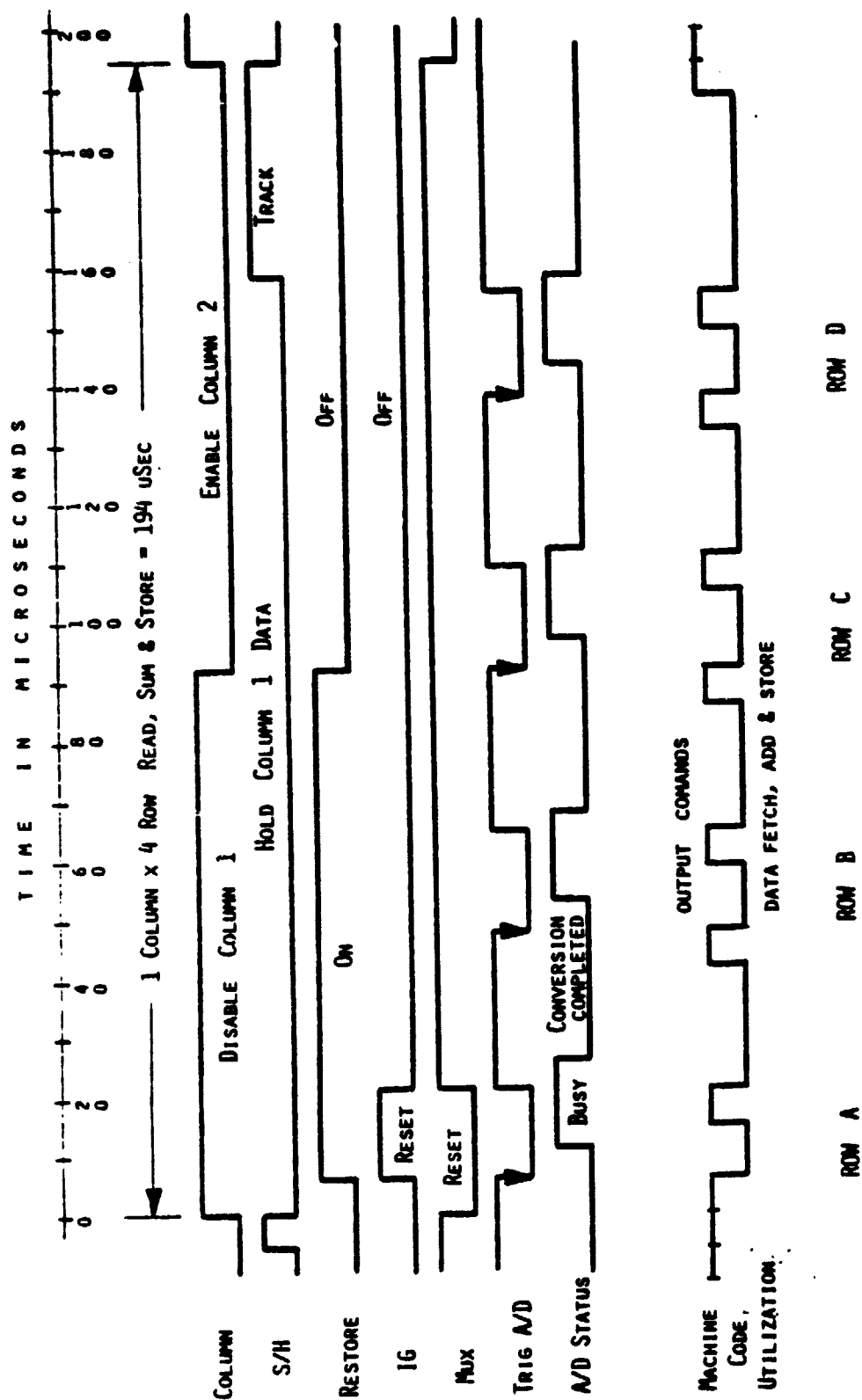


FIGURE 5  
CID COLUMN TIMING

are stored by the sample-and-hold circuits after a number of pre-amp time constraints have elapsed. At this point the column line is disabled, transferring the signal charge back to the collection sites. The IG line is pulsed to reset the CID output lines to the reference voltage for the next readout cycle.

A combination multiplexer and analog-to-digital converter module is used to read the signals from each sample-and-hold and provide a 12 bit digital output to the microprocessor. Control signals are required to reset the multiplexer channel pointer and initiate each conversion cycle. The module is configured such that the channel pointer is automatically advanced after each conversion.

Since the microprocessor has an 8-bit data bus, the 12-bit data is split into two byte segments. Thus two separate input operations are required per pixel. In addition, the baseline signal processing scheme incorporates noise reduction by averaging successive readings of the same pixel (see logic flow diagram in Figure 6). Rather than store each reading separately and processing it later, significant savings in memory and even execution time is realized by maintaining a 2 byte running sum per row during the data collection operation.

Also shown in Figure 5 is the timing associated with the microprocessor machine code. Operating with a one megahertz clock, the 6502  $\mu$ P execution times vary from two microseconds for an immediate accumulator load to six microseconds identical for each of the four rows, resulting in a column



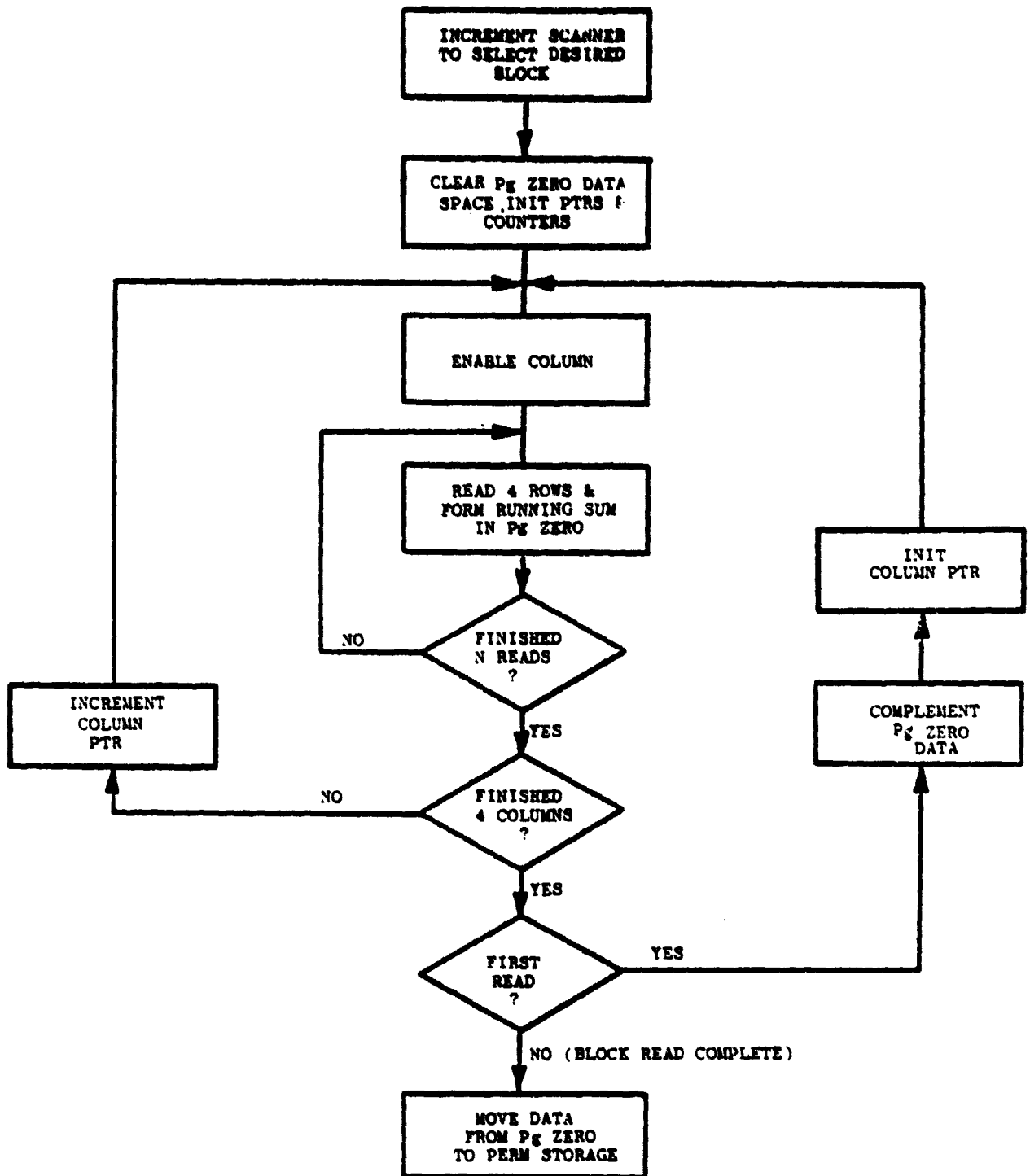


FIGURE 6  
READ-ONE-BLOCK LOGIC FLOW DIAGRAM

read time of 194 microseconds (or 48 microseconds per pixel). Since additional time is required for setup operations (i.e., injection of previous signal, block and column selection, etc.) it is anticipated that the minimum time to read an entire array (1024 blocks) is less than 800 milliseconds.